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(71)Applicant : SEIWA ELECTRIC MFG CO LTD

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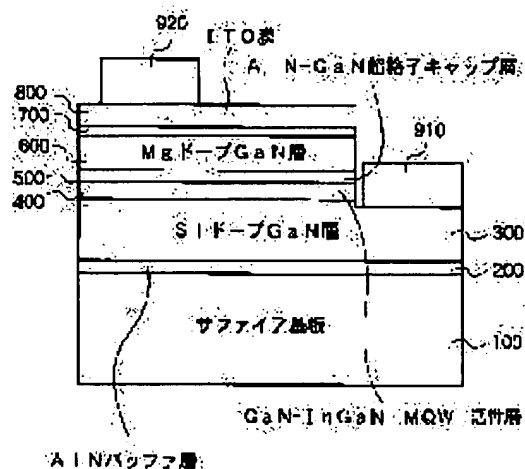
(72)Inventor : TOKUJI SHIGEKAZU
YAMAJI TAHEI

(54) GALLIUM NITRIDE SEMICONDUCTOR LIGHT EMITTING ELEMENT AND MANUFACTURING METHOD THEREFOR

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a gallium nitride semiconductor light emitting element which is superior in mechanical strength, which is not easily deteriorated even in high temperature/high humidity environment, and which has the high take-out efficiency of light to an outer part.

SOLUTION: A gallium nitride semiconductor light emitting element is provided, having an ITO film whose film thickness is 100 \AA or more as a current diffusion layer, where at least its first layer is formed on a P-type GaN semiconductor layer by a vacuum vapor deposition method.



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